

**Notice of References Cited**

Application/Control No.

09/160,657

Applicant(s)/Patent Under  
Reexamination  
LYDING ET AL.

Examiner

Jeff Vockrodt

Art Unit

2822

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**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
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**FOREIGN PATENT DOCUMENTS**

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	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Okazaki et al., "Characteristics of Sub-1/4- $\mu$ m Gate Surface Channel PMOSFET's Using a Multilayer Gate Structure of Boron-Doped Poly-Si on Thin Nitrogen-Doped Poly-Si," IEEE Transactions of Electron Devices, Vol. 41, No. 12, December 1994, pp. 2369-2375
	V	
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	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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